





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary (Typ. @ VGS = -4.5V, TA = +25°C)

BVDSS	RDS(ON)	Qg	Q _{gd}	lσ
-12V	85mΩ	3.7nC	0.6nC	-2.6A

Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery managements
- Load switches
- Battery protections

Features

- LD-MOS Technology with the Lowest Figure of Merit: $R_{DS(ON)} = 85m\Omega$ to Minimize On-State Losses $Q_q = 3.7nC$ for Ultra-Fast Switching
- V_{GS(TH)} = -0.6V Typ. for a Low Turn-On Potential
- CSP with Footprint 1.0mm x 1.0mm
- Height = 0.62mm for Low Profile
- ESD = 3kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

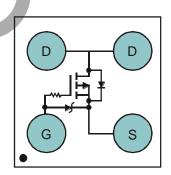
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: U-WLB1010-4
- Terminal Connections: See Diagram Below
 - Weight: 0.005 grams (Approximate)

U-WLB1010-4





Top View Equivalent Circuit

Ordering Information (Note 4)

Part Number	Backage	Pac	king
Fait Number	Package	Qty.	Carrier
DMP1096UCB4-7	U-WLB1010-4	3000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



1W = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022) M = Month (ex: 9 = September)



BW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Kev

Year	2010		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Х		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	-12	V
Gate-Source Voltage			Vgss	-5	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	lD	-2.6 -2.1	А
Continuous Drain Current (Note 5) V _{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	lp	-2.4 -1.9	Α
Pulsed Drain Current (Note 6)			I _{DM}	-10	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.82	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	150	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.

6. Repetitive rating, pulse width limited by junction temperature.

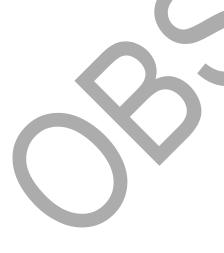


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

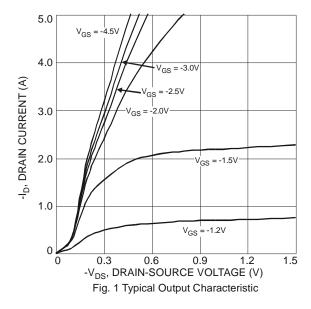
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Gate-Source Breakdown Voltage		-6.0	_	_	V	$V_{DS} = 0V, I_{G} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	-	_	-1	μΑ	V _{DS} = -9.6V, V _{GS} = 0V	
Gate-Source Leakage	Igss	-	_	-500	nA	$V_{GS} = -5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-0.6	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	85	102		$V_{GS} = -4.5V, I_D = -500mA$	
Static Drain-Source On-Resistance	RDS(ON)	_	97	116	mΩ	$V_{GS} = -2.5V$, $I_{D} = -500$ mA	
		_	127	152		Vgs = -1.5V, I _D = -500mA	
Forward Transfer Admittance	Y _{fs}	_	4	_	S	V _{DS} = -6V, I _D = -500mA	
Diode Forward Voltage	VsD	_	-0.6	-1.0	V	V _G S = 0V, I _S = -500mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		251	_		V 9V V 9V	
Output Capacitance	Coss	-	359	_	pF	$V_{DS} = -6V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		70	_		1 = 1.01VII 12	
Total Gate Charge	Q_g		3.7				
Gate-Source Charge	Q_{gs}	_	0.4		nC	VGS = -4.5V, VDS = -6V	
Gate-Drain Charge	Q_{gd}	_	0.6	/ –	IIC	$I_D = -500 \text{mA}$	
Gate Charge at Vth	Q _{g(th)}	_	0.2	_			
Turn-On Delay Time	td(ON)	_	17.6	-			
Turn-On Rise Time	t _R	_	26.9			V _{DS} = -6V, V _{GS} = -2.5V	
Turn-Off Delay Time	tD(OFF)	-	37.5	_	ns	$R_G = 20\Omega$, $I_D = -500mA$	
Turn-Off Fall Time	tF		32.3	_			

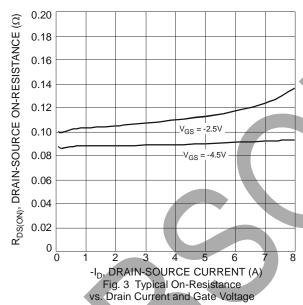
Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.









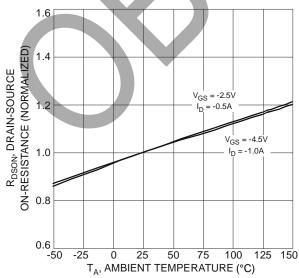
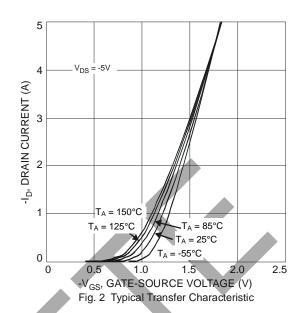
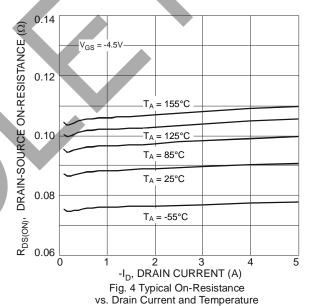


Fig. 5 On-Resistance Variation with Temperature





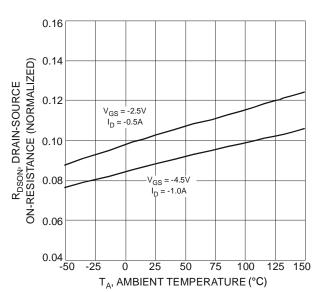


Fig. 6 On-Resistance Variation with Temperature



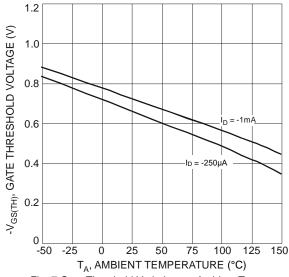
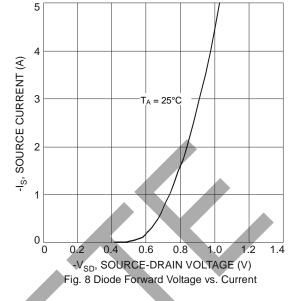
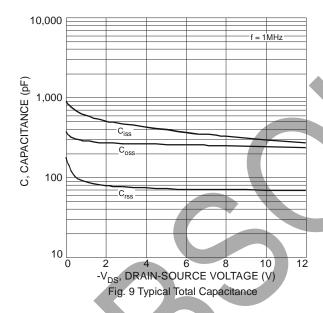


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





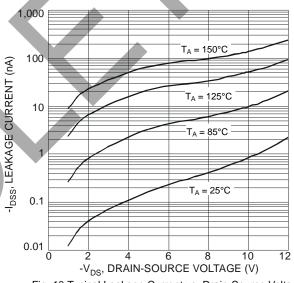


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

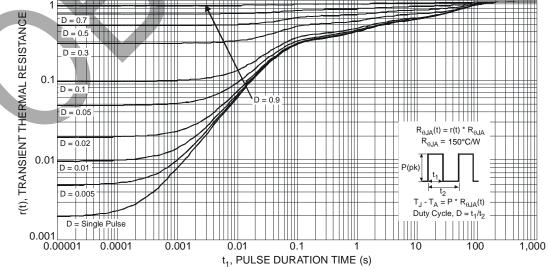


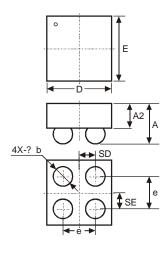
Fig. 11 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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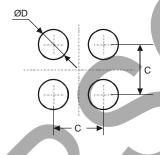


	U-WLB1010-4						
Dim	Min	Max	Тур				
D	0.95	1.05	1.00				
Е	0.95	1.05	1.00				
Α	-	0.62	_				
A2	_	_	0.38				
b	0.25	0.35	0.30				
е	-	-	0.50				
SD	_	_	0.25				
SE	_	-	0.25				
All	Dimens	ions in r	nm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-WLB1010-4



Dimensions	Value (in mm)
С	0.50
D	0.25



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